



# BYT60P-1000 BYT261PIV-1000

## FAST RECOVERY RECTIFIER DIODES

### MAJOR PRODUCT CHARACTERISTICS

$I_{F(AV)}$	<b>2 x 60 A</b>
$V_{RRM}$	<b>1000 V</b>
$V_F(\text{max})$	<b>1.8 V</b>
$t_{rr}(\text{max})$	<b>70 ns</b>

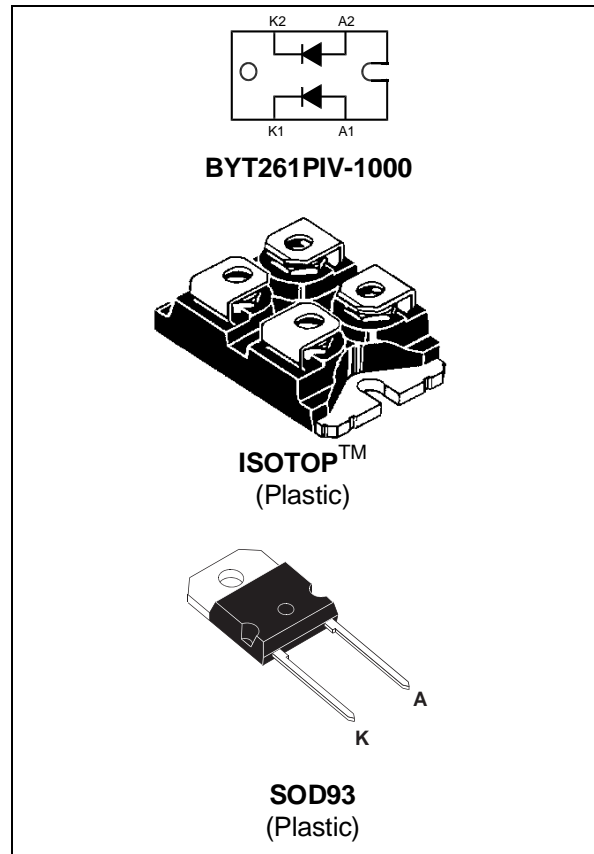
### FEATURES AND BENEFITS

- VERY LOW REVERSE RECOVERY TIME
- VERY LOW SWITCHING LOSSES
- LOW NOISE TURN-OFF SWITCHING
- INSULATED PACKAGE: ISOTOP  
Insulation voltage: 2500 V<sub>RMS</sub>  
Capacitance = 45 pF  
Inductance < 5 nH

### DESCRIPTION

Dual or high single voltage rectifier devices suited for Switch Mode Power Supplies and other power converters.

These devices are packaged in ISOTOP or in SOD93.



### ABSOLUTE RATINGS (limiting values, per diode)

Symbol	Parameter		Value	Unit
$V_{RRM}$	Repetitive peak reverse voltage		1000	V
$I_{FRM}$	Repetitive peak forward current	$t_p=5\ \mu\text{s}$ $F=1\text{kHz}$	1000	A
$I_{F(RMS)}$	RMS forward current	ISOTOP	140	A
		SOD93	100	
$I_{F(AV)}$	Average forward current $\delta = 0.5$	$T_c = 50^\circ\text{C}$ ISOTOP	60	A
		$T_c = 60^\circ\text{C}$ SOD93	60	
$I_{FSM}$	Surge non repetitive forward current	$t_p = 10\ \text{ms}$ Sinusoidal	400	A
$T_{stg}$	Storage temperature range		- 40 to + 150	$^\circ\text{C}$
$T_j$	Maximum operating junction temperature		150	$^\circ\text{C}$

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### THERMAL RESISTANCES

Symbol	Parameter		Value	Unit	
$R_{th(j-c)}$	Junction to case	ISOTOP	Per diode Total	0.8 0.45	°C/W
		SOD93	Total	0.7	
$R_{th(c)}$			Coupling	0.1	°C/W

When the diodes 1 and 2 are used simultaneously :

$$\Delta T_j(\text{diode 1}) = P(\text{diode 1}) \times R_{th(j-c)} (\text{Per diode}) + P(\text{diode 2}) \times R_{th(c)}$$

### STATIC ELECTRICAL CHARACTERISTICS (per diode)

Symbol	Parameter	Test Conditions		Min.	Typ.	Max.	Unit
$V_F$ *	Forward voltage drop	$T_j = 25^\circ\text{C}$	$I_F = 60\text{ A}$			1.9	V
		$T_j = 100^\circ\text{C}$				1.8	
$I_R$ **	Reverse leakage current	$T_j = 25^\circ\text{C}$	$V_R = V_{RRM}$			100	$\mu\text{A}$
		$T_j = 100^\circ\text{C}$				6	mA

Pulse test : \*  $t_p = 380\ \mu\text{s}$ ,  $\delta < 2\%$

\*\*  $t_p = 5\ \text{ms}$ ,  $\delta < 2\%$

To evaluate the conduction losses use the following equation:

$$P = 1.47 \times I_{F(AV)} + 0.005 I_{F(RMS)}^2$$

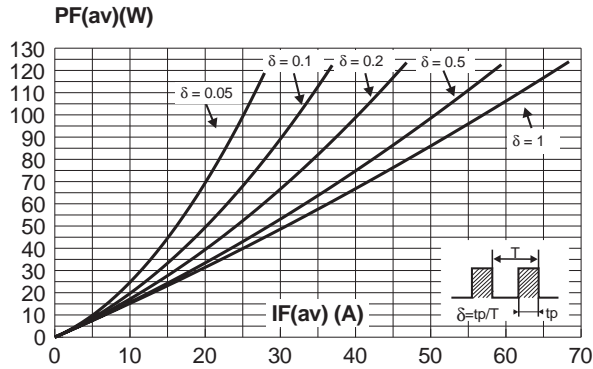
### RECOVERY CHARACTERISTICS (per diode)

Symbol	Test Conditions		Min.	Typ.	Max.	Unit
$t_{rr}$	$T_j = 25^\circ\text{C}$	$I_F = 1\text{ A}$ $V_R = 30\text{ V}$ $dI_F/dt = -15\text{ A}/\mu\text{s}$			170	ns
		$I_F = 0.5\text{ A}$ $I_R = 1\text{ A}$ $I_{rr} = 0.25\text{ A}$			70	

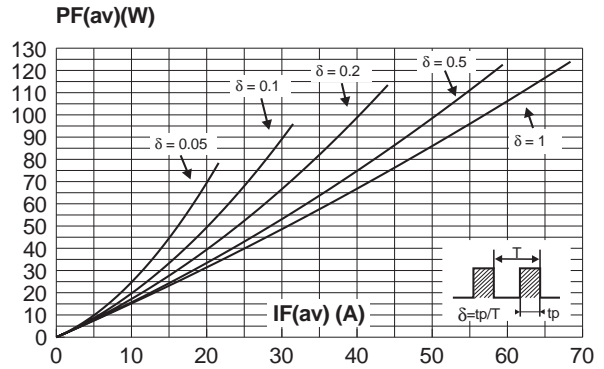
### TURN-OFF SWITCHING CHARACTERISTICS

Symbol	Parameter	Test Conditions		Min.	Typ.	Max.	Unit
$t_{IRM}$	Maximum reverse recovery time	$dI_F/dt = -240\ \text{A}/\mu\text{s}$	$V_{CC} = 200\ \text{V}$ $I_F = 60\ \text{A}$ $L_p \leq 0.05\ \mu\text{H}$ $T_j = 100^\circ\text{C}$ (see fig. 13)			200	ns
		$dI_F/dt = -480\ \text{A}/\mu\text{s}$				120	
$I_{RM}$	Maximum reverse recovery current	$dI_F/dt = -240\ \text{A}/\mu\text{s}$	$V_{CC} = 200\ \text{V}$ $I_F = I_{F(AV)}$ $L_p = 2.5\ \mu\text{H}$ (see fig. 14)			40	A
		$dI_F/dt = -480\ \text{A}/\mu\text{s}$				44	
$C = \frac{V_{RP}}{V_{CC}}$	Turn-off overvoltage coefficient	$T_j = 100^\circ\text{C}$ $V_{CC} = 200\text{ V}$ $I_F = I_{F(AV)}$ $dI_F/dt = -60\text{ A}/\mu\text{s}$ $L_p = 2.5\ \mu\text{H}$ (see fig. 14)			3.3	4.5	/

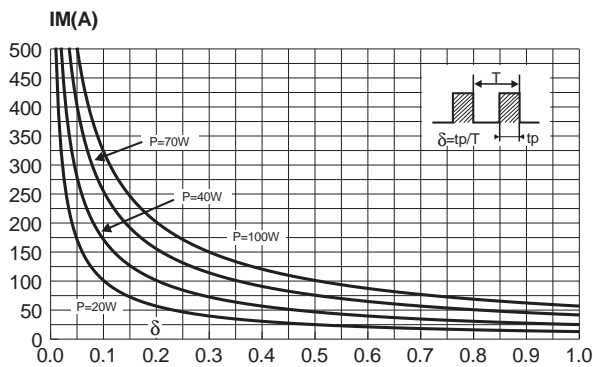
**Fig. 1-1:** Average forward power dissipation versus average forward current (per diode, ISOTOP).



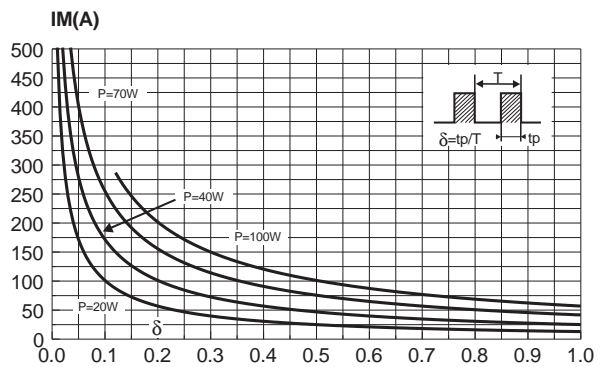
**Fig. 1-2:** Average forward power dissipation versus average forward current (SOD93).



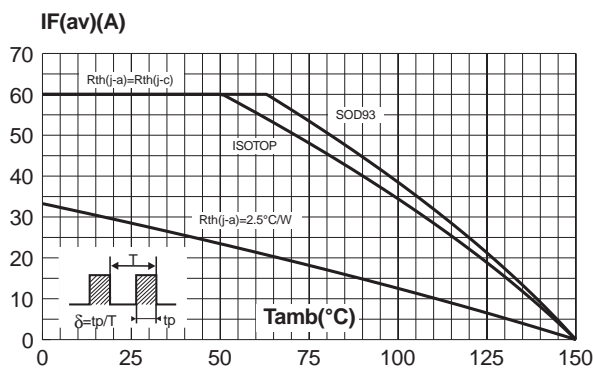
**Fig. 2-1:** Peak current versus form factor (per diode, ISOTOP).



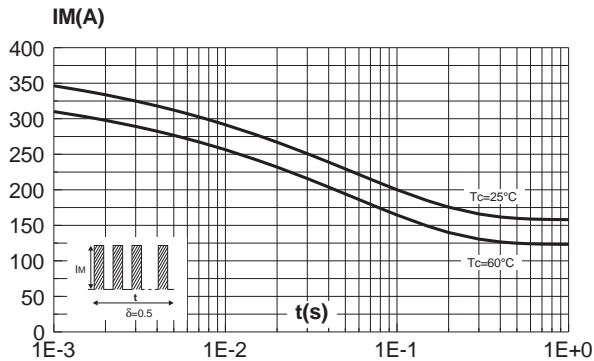
**Fig. 2-2:** Peak current versus form factor (SOD93).



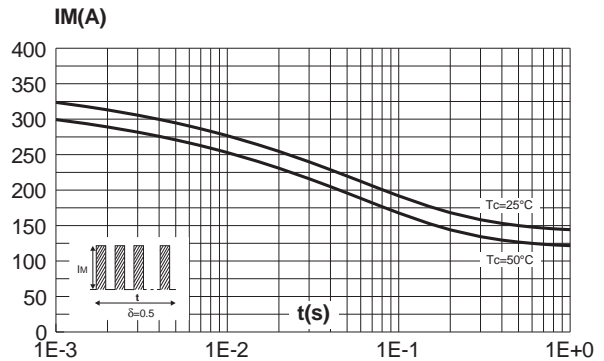
**Fig. 3:** Average forward current versus ambient temperature ( $\delta=0.5$ , per diode for ISOTOP).



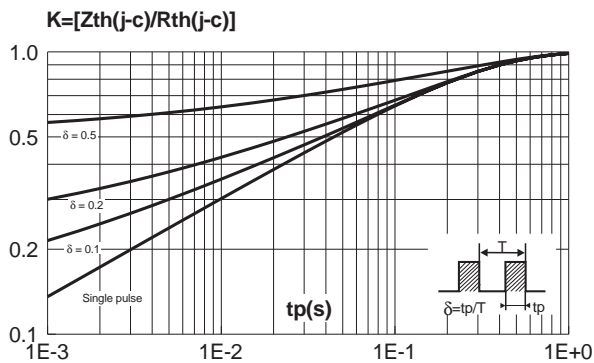
**Fig. 4-1:** Non repetitive surge peak forward current versus overload duration (SOD93).



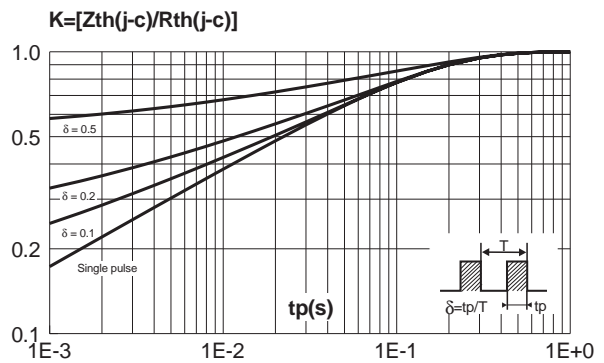
**Fig. 4-2:** Non repetitive surge peak forward current versus overload duration (per diode, ISOTOP).



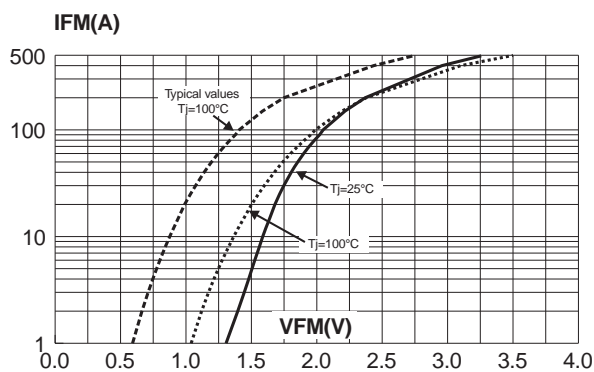
**Fig. 5-1:** Relative variation of thermal impedance junction to case versus pulse duration (per diode, ISOTOP).



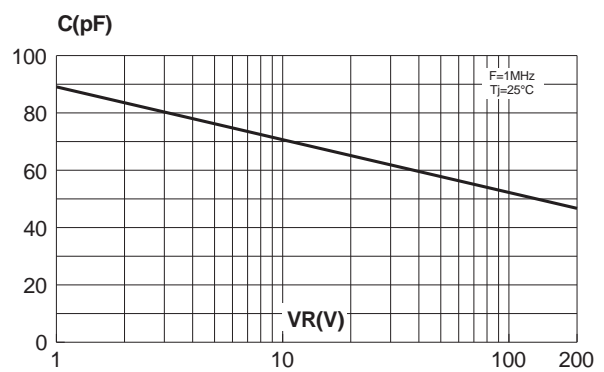
**Fig. 5-2:** Relative variation of thermal impedance junction to case versus pulse duration (SOD93).



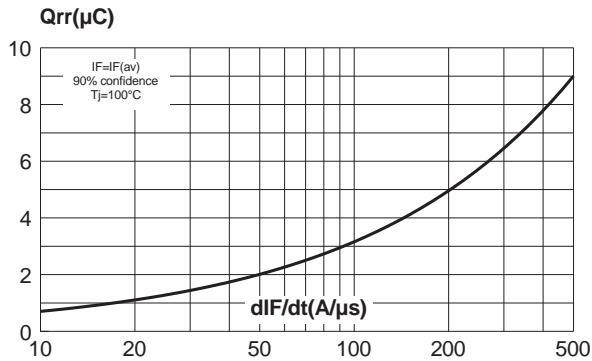
**Fig. 6:** Forward voltage drop versus forward current (maximum values, per diode for ISOTOP).



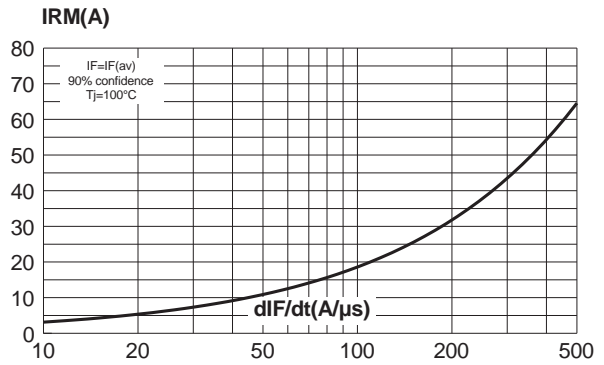
**Fig. 7:** Junction capacitance versus reverse voltage applied (typical values, per diode for ISOTOP).



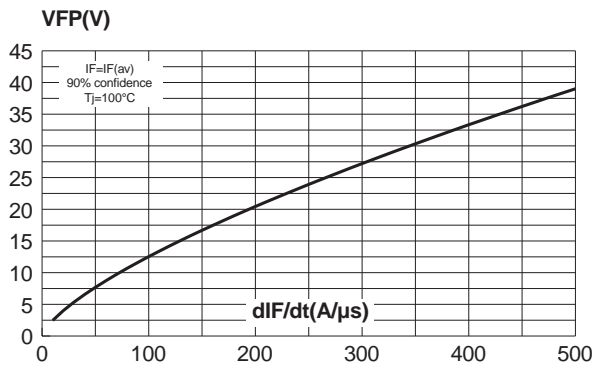
**Fig. 8:** Recovery charges versus  $dl_F/dt$  (per diode for ISOTOP).



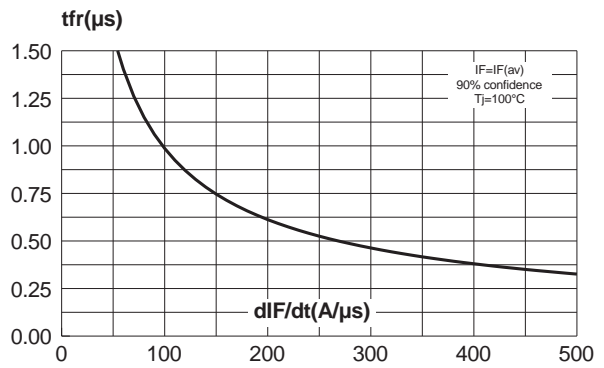
**Fig. 9:** Recovery current versus  $dl_F/dt$  (per diode for ISOTOP).



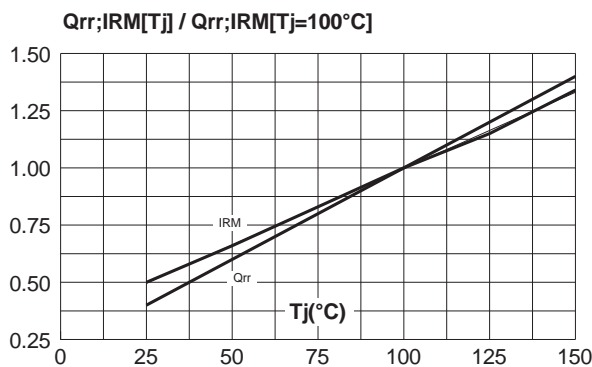
**Fig. 10:** Transient peak forward voltage versus  $dl_F/dt$  (per diode for ISOTOP).



**Fig. 11:** Forward recovery time versus  $dl_F/dt$  (per diode for ISOTOP).

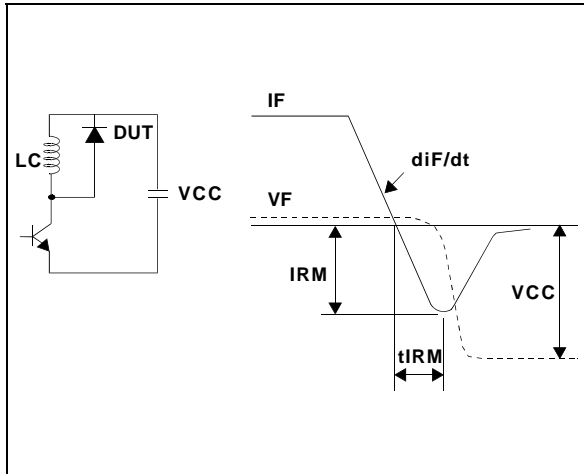


**Fig. 12:** Dynamic parameters versus junction temperature.

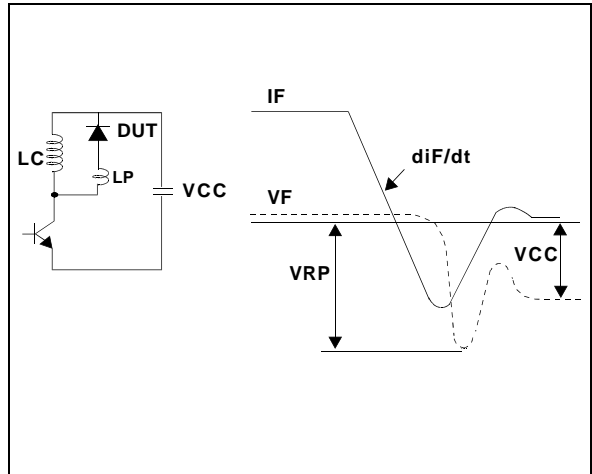


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**Fig. 13:** Turn-off switching characteristics (without serie inductance).

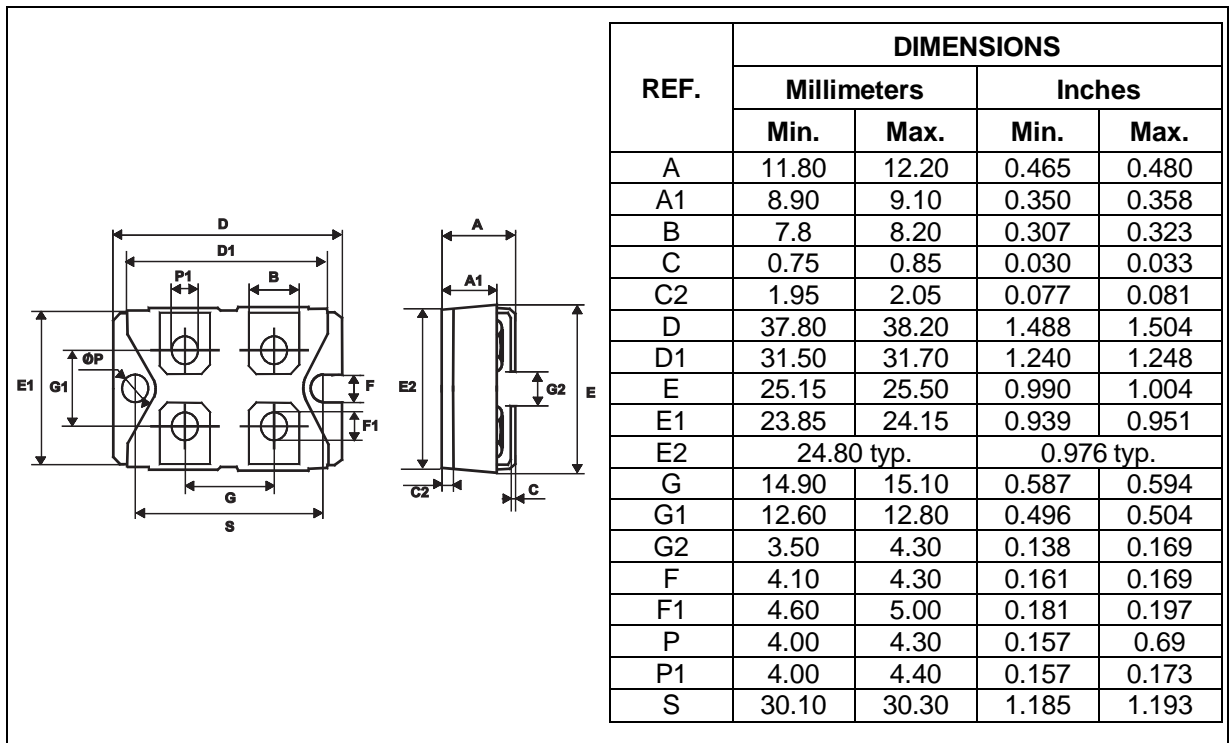


**Fig. 14:** Turn-off switching characteristics (with serie inductance).



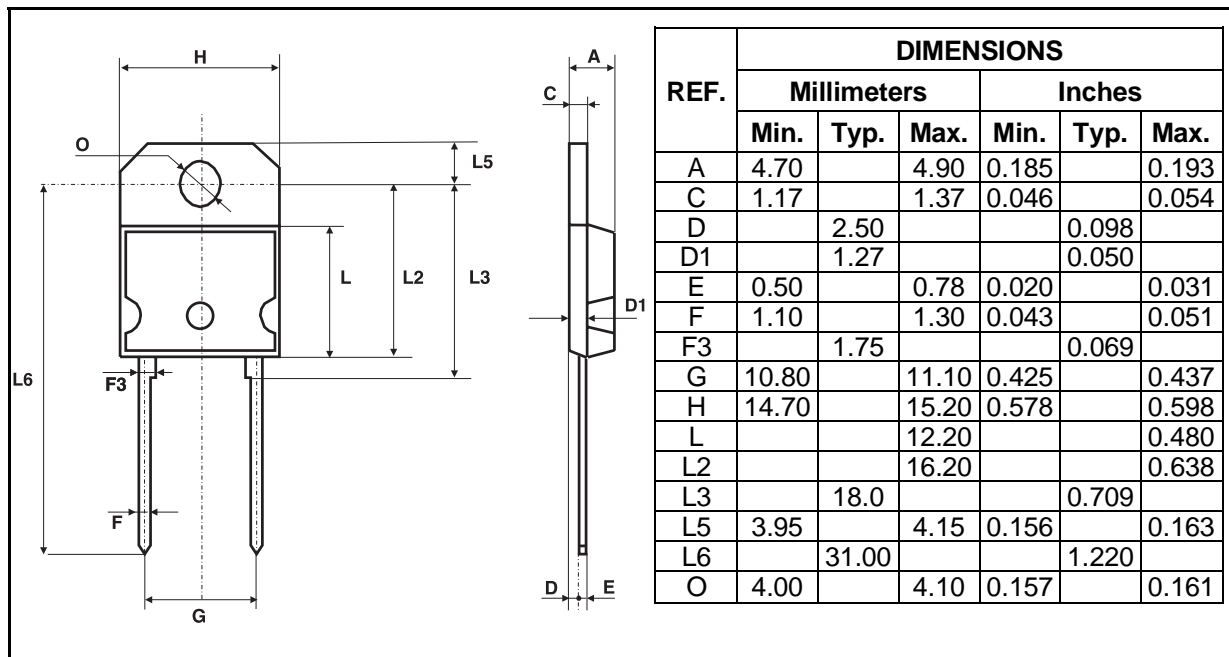
## PACKAGE MECHANICAL DATA

### ISOTOP



**PACKAGE MECHANICAL DATA**

SOD93 Plastic



Ordering type	Marking	Package	Weight	Base qty	Delivery mode
BYT60P-1000	BYT60P-1000	SOD93	3.79 g.	30	Tube
BYT261PIV-1000	BYT261PIV-1000	ISOTOP	28 g. (without screws)	10	Tube

- Cooling method: by conduction (C)
- Recommended torque value (ISOTOP): 1.3 N.m (MAX 1.5 N.m) for the 6 x M4 screws. (2 x M4 screws recommended for mounting the package on the heatsink and the 4 screws given with the screw version). The screws supplied with the package are adapted for mounting on a board (or other types of terminals) with a thickness of 0.6 mm min and 2.2 mm max.
- Recommended torque value (SOD93): 0.8 N.m.
- Maximum torque value (SOD93): 1.0 N.m.
- Epoxy meets UL94,V0

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